

247252US2SDIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

KEIJI HOSOTANI :

SERIAL NO: NEW DIV APPLICATION :

FILED: HEREWITH :

FOR: SEMICONDUCTOR MEMORY DEVICE UTILIZING TUNNEL MAGNETO  
RESISTIVE EFFECTS AND METHOD FOR MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VA 22313

SIR:

Prior to examination on the merits, please amend the above-identified divisional application as follows:

**Amendment to the Specification** begins on page 2.

**Amendments to the Claims** begin on page 3 of this paper.

**Remarks/Arguments** begin on page 7 of this paper.